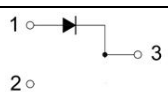
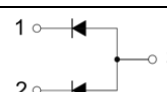


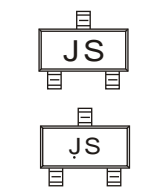
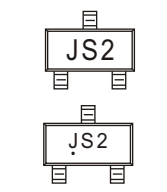
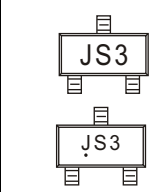
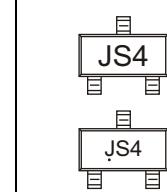


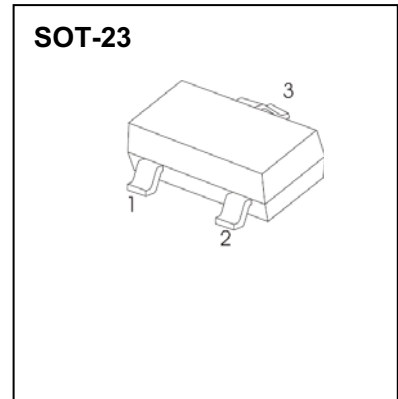
SOT-23 Plastic-Encapsulate Diodes

BAS21/A/C/S SWITCHING DIODE

FEATURES

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications
- High Conductance

BAS21	BAS21A	BAS21C	BAS21S
			
MARKING: JS	MARKING: JS2	MARKING: JS3	MARKING: JS4
			



Solid dot = Green molding compound device, if none, the normal device

Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Repetitive peak reverse voltage	V_{RRM}	250	V
Working peak reverse voltage	V_{RWM}		
DC blocking voltage	V_R		
Forward continuous current	I_{FM}	400	mA
Average rectified output current	I_O	200	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}		A
Repetitive peak forward surge current	I_{FRM}		mA
Power dissipation	P_D		mW
Thermal resistance junction to ambient	R_{JA}		°C/W
Junction temperature	T_J	1	°C
Storage temperature range	T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	250		V
Reverse voltage leakage current	I_R	$V_R=200V$		0.1	μA
Forward voltage	V_F	$I_F=100mA$ $I_F=200mA$		1000 1250	mV
Diode capacitance	C_D	$V_R=0V, f=1MHz$		5	pF
Reverse recovery time	t_{rr}	$I_F=I_R=30mA, I_{rr}=0.1 \times I_R, R_L=100\Omega$		50	n

Typical Characteristics

